

## WBFBP-03B Plastic-Encapsulate Transistors

### TK3904NND03 TRANSISTOR

#### DESCRIPTION

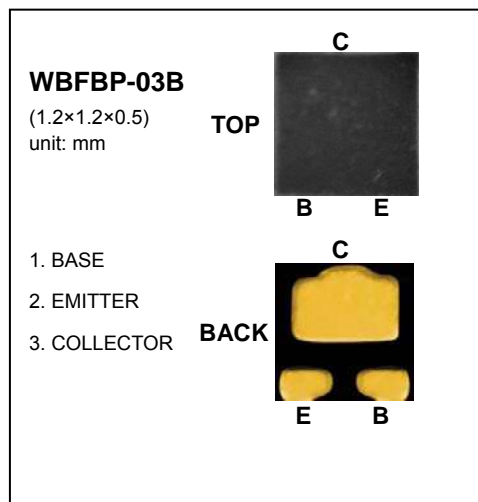
NPN Epitaxial Silicon Transistor

#### FEATURES

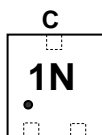
Epitaxial Planar Die Construction  
Complementary PNP Type Available (TK3906NND03)  
Ultra-Small Surface Mount Package  
Also Available in Lead Free Version

#### APPLICATION

General Purpose Amplifier, switching  
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



#### MARKING:1N



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#### MAXIMUM RATINGS( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	0.2	A
$P_C$	Collector Dissipation	0.15	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CEX}$	$V_{CE}=30\text{V}, V_{EB(off)}=3\text{V}$			0.05	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
	$V_{CE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	$f_T$	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz			4	pF
Noise figure	NF	V <sub>CE</sub> =5V, I <sub>c</sub> =0.1mA,			5	dB
Delay time	t <sub>d</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =-0.5V, I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Rise time	t <sub>r</sub>				35	ns
Storage time	t <sub>S</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA			200	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> = 1mA			50	ns